



A Product Line of Diodes Incorporated



ZXM64P03X

30V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	Max R _{DS(on)}	Max I _D T _A = 25°C	
-30V	75mΩ @ V _{GS} = -10V	-3.8A	
	100m Ω @ V _{GS} = -4.5V	-3.3A	

Description

This MOSFET utilizes a unique structure that combines the benefits of low on-resistance with fast switching speed, making it ideal for high-efficiency power management applications.

Applications

- DC DC converters
- Power management functions
- Disconnect switches
- Motor control

Features

- Fast switching speed
- Low on-resistance
- Low threshold
- Low gate drive
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

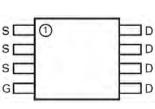
Mechanical Data

- Case: MSOP8
- Case Material: Molded Plastic, UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish; Solderable per MIL-STD-202, Method 208 3
- Weight: 0.028 grams (approximate)



MSOP8

Top View



Top View

Pin Out

G

Equivalent Circuit

D

Ordering Information (Note 4)

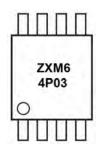
Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXM64P03XTA	ZXM64P03	7	12	1,000 Units

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com.

Marking Information



ZXM64P03 = Product Type Marking Code





Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V _{DSS}	-30	V
Gate-Source Voltage			V _{GS}	±20	V
Continuous Drain Current	V _{GS} = 4.5V	$T_A = +25^{\circ}C$ (Note 5) $T_A = +70^{\circ}C$ (Note 5)	ID	-3.8 -3.0	A
Pulsed Drain Current (Note 7)			I _{DM}	-1.9	А
Continuous Source Current (Body Diode) (Note 6)			Is	-2.3	А
Pulsed Source Current (Body Diode) (Note 7)			I _{SM}	-19	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5) Linear Derating Factor	P _D	1.1 8.8	W mW/°C
Power Dissipation (Note 6) Linear Derating Factor	PD	1.8 14.4	W mW/°C
Thermal Resistance, Junction to Ambient (Note 5)	R _{0JA}	113	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	R _{0JA}	70	°C/W
Thermal Resistance, Junction to Ambient (Note 8)	R _{θJL}	39.8	°C/W
Operating and Storage Temperature Range	T _{J,} T _{STG}	-55 to +150	C°

5. For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions

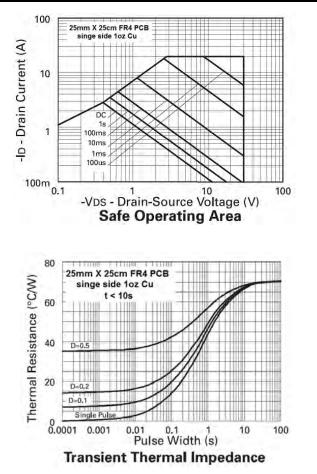
6. For a device surface mounted on FR4 PCB measured at t ≤10 secs.

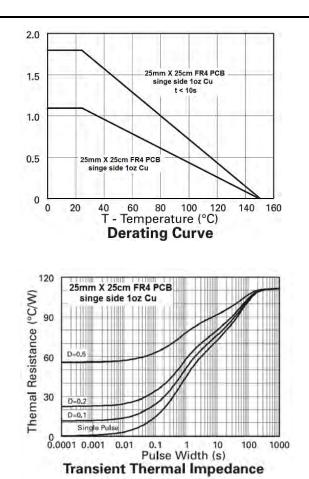
7. Repetitive rating pulse width limited by pulse current limited by maximum junction temperature.

8. Thermal resistance from junction to solder-point (at the end of the Drain lead).

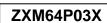
Thermal Characteristics

Notes:









Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS	1 - 2 1						
Drain-Source Breakdown Voltage	BV _{DSS}	-30	_	_	V	$I_D = -250 \mu A, V_{GS} = 0 V$	
Zero Gate Voltage Drain Current	IDSS	_	_	-1	μΑ	$V_{DS} = -30V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS	· · ·						
Gate Threshold Voltage	V _{GS(th)}	-1.0	—	—	V	$I_D = -250 \mu A$, $V_{DS} = V_{GS}$	
Static Drain-Source On-Resistance (Note 9)	P			75	mΩ	$V_{GS} = -10V, I_D = -2.4A$	
Static Dialit-Source Off-Resistance (Note 9)	R _{DS (ON)}			100		$V_{GS} = -4.5V, I_D = -1.2A$	
Forward Transconductance (Notes 9 and 11)	g fs	2.3	_	_	S	$V_{DS} = -10V, I_D = -1.2A$	
Diode Forward Voltage (Note 9)	V _{SD}	_	_	-0.95	V	$T_J = +25^{\circ}C, I_S = -2.4A, V_{GS} = 0V$	
Reverse Recovery Time (Note 11)	t _{rr}	_	30.2	-	ns	$T_J = +25^{\circ}C, I_F = -2.4A,$	
Reverse Recovery Charge (Note 11)	Q _{rr}	_	27.8	_	nC	di/dt = 100A/µs	
DYNAMIC CHARACTERISTICS (Note 11)							
Input Capacitance	C _{iss}	_	825	_		$V_{DS} = -25V, V_{GS} = 0V$ f = 1.0MHz	
Output Capacitance	C _{oss}	_	250	_	pF		
Reverse Transfer Capacitance	C _{rss}	_	80	_			
Turn-On Delay Time (Note 10)	t _{d(on)}	_	4.4	_			
Turn-On Rise Time (Note 10)	tr	_	6.2	_	ns	$V_{DD} = -15V, I_D = -2.4A,$ $R_G = 6.2\Omega, R_D = 6.2\Omega$ (Refer to test circuit)	
Turn-Off Delay Time (Note 10)	t _{d(off)}	_	40	_			
Turn-Off Fall Time (Note 10)	t _f	_	29.2	_	1		
Total Gate Charge (Note 10)	Qg	_	_	46		$V_{DS} = -24V, V_{GS} = -10V,$ $I_{D} = -2.4A$	
Gate-Source Charge (Note 10)	Q _{gs}	_		9	nC		
Gate-Drain Charge (Note 10)	Q _{gd}	_		11.5]	(Refer to test circuit)	

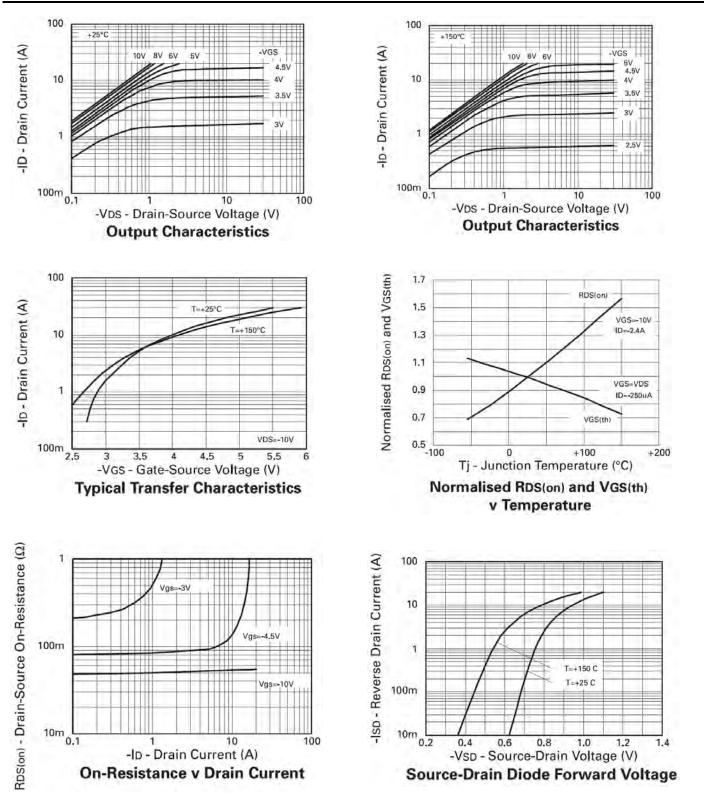
Notes: 9. Measured under pulsed conditions. Pulse width = 300μ s. Duty cycle $\leq 2\%$.

Switching characteristics are independent of operating junction temperature.
For design aid only, not subject to production testing.

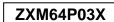




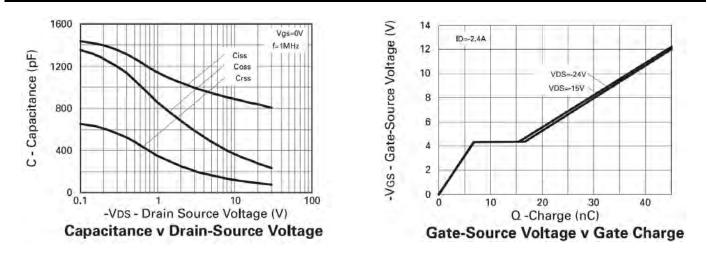
Typical Characteristics



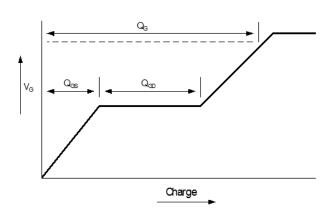




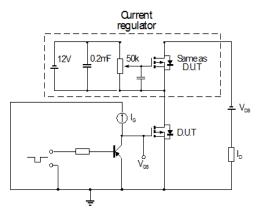
Typical Characteristics - continued



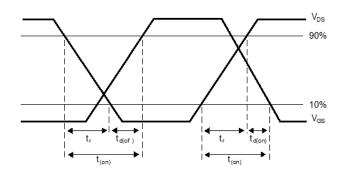
Test Circuits



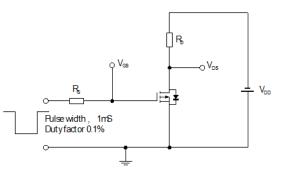
Basic gate charge waveform



Gate charge test circuit



Switching time waveforms



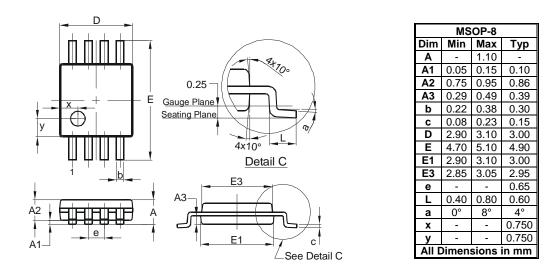
Switching time test circuit



ZXM64P03X

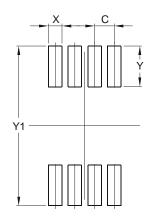
Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	0.650
Х	0.450
Y	1.350
Y1	5.300





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